Solid State Devices, Inc.
14830 Valley View Blvd * La Mirada, Ca 90638
Phone: (562) 404-7855 * Fax: (562) 404-1773
ssdi@ssdi-power.com * www.ssdi-power.com

SFT4957A2
Series

Dual Microminiature Package
30 mA 30 Volts
Dual PNP RF Transistor

DESIGNER'S DATA SHEET

Part Number / Ordering Information [1/]

SFT4957A2

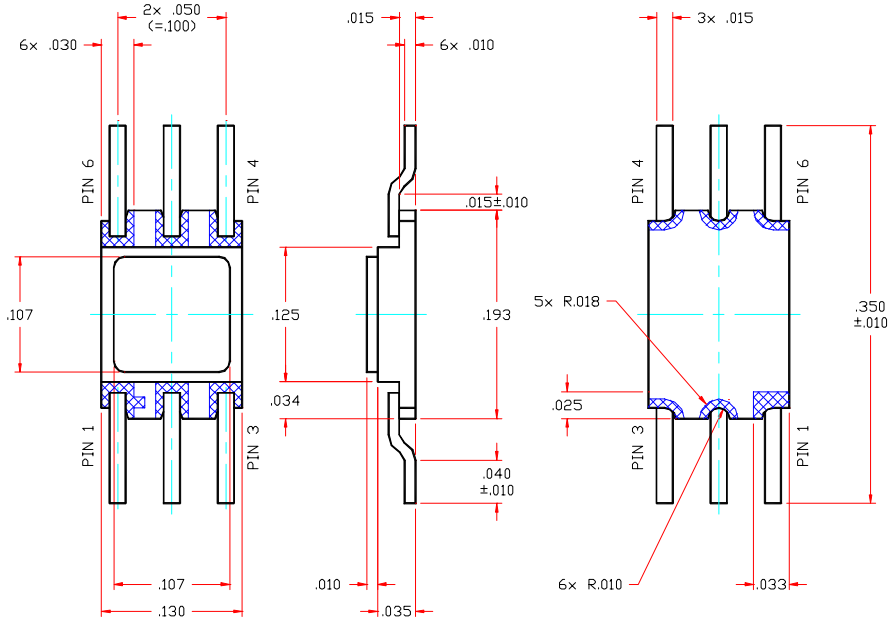
Screening [2/] __ = Commercial
TX = TX Level
TXV = TXV Level
S = S Level

Package: GW = Gullwing

Features:
- RF Switching Transistor
- Multiple Devices Reduce Board Space
- Replacement/Enhancement for 2N4957UB
- TX, TXV, S-Level screening available
- NPN complimentary parts available (SFT2857A2)

Maximum Ratings	Symbol	Value	Units
Collector – Emitter Voltage	V_{CEO}	30	Volts
Collector – Base Voltage	V_{CBO}	30	Volts
Emitter – Base Voltage	V_{EBO}	3	Volts
Continues Collector Current	I_C	30	mAmps
Power Dissipation @ TC = 25ºC (each device)	P_D	200	mW
Operating & Storage Temperature	Top & Tstg	-65 to +200	ºC
Maximum Thermal Resistance (Junction to PCB)	$R_{\theta JC}$	290	ºC/W

Gullwing (GW)



NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: TR0077 A

Doc

Solid State Devices, Inc.
14830 Valley View Blvd * La Mirada, Ca 90638
Phone: (562) 404-7855 * Fax: (562) 404-1773
ssdi@ssdi-power.com * www.ssdi-power.com

SFT4957A2 Series

Electrical Characteristic [4/]		Symbol	Min	Max	Units
Collector – Emitter Sustaining Voltage	I_C = 1 mA	BV_{CEO}	-30	—	Volts
Collector Cutoff Current	Vcb = -20 V	I_{CBO1}	—	100	nA
Collector Cutoff Current	Vcb = -30 V	I_{CBO2}	—	100	uA
Collector Cutoff Current	Vcb = -20 V, Ta= 150ºC	I_{CBO3}	—	100	uA
Emitter Cutoff Current	Veb = -3.0 V	I_{EBO}	—	100	uA
DC Forward Current Transfer Ratio *	V_{CE} = -10V, I_C = 0.5 mA V_{CE} = -10V, I_C = 2.0 mA V_{CE} = -10V, I_C = 5 mA V_{CE} = -10V, I_C =5 mA, Ta= -55ºC	H_{FE1} H_{FE2} H_{FE3} H_{FE4}	15 20 30 10	— — 165 —	
Frequency Transition (Small Signal Current Gain) @ f= 100 MHz	V_{CE} = -10V, I_C = 2.0 mA	h_{fe}	12	36	
CB feedback (output) Capacitance	V_{CE} = -10V, f = 1MHz	c_{cb}	—	0.8	pF
CB time constant	V_{CE} =-10V, I_C =2mA, f= 63.6 MHz	**rbCc**	1.0	16	psec
Common emitter small signal power gain	V_{CE} =-10V, I_C = 2mA, f= 450 MHz	G_{pe}	17	25	dB
Noise Figure	Ic = 2 mA, Vce = -10 V, RL = 50Ω, f = 450 MHz	**NF**	—	3.5	dB

NOTES:

* Pulse Test: Pulse Width = 300µsec, Duty Cycle = 2%

1/ For Ordering Information, Price, and Availability Contact Factory.

2/ Screening per MIL-PRF-19500

3/ For Package Outlines Contact Factory.

4/ Unless Otherwise Specified, All Electrical Characteristics @25ºC.

Available Part Numbers:

SFT4957A2GW

PIN ASSIGNMENT						
Package	**Pin 1**	**Pin 2**	**Pin 3**	**Pin 4**	**Pin 5**	**Pin 6**
GW	Collector1	Base1	Emitter1	Collector2	Base2	Emitter2